



# RF Power LDMOS Transistor

## N-Channel Enhancement-Mode Lateral MOSFET

This 28 W asymmetrical Doherty RF power LDMOS transistor is designed for cellular base station applications requiring very wide instantaneous bandwidth capability covering the frequency range of 1880 to 2025 MHz.

### 1880–2025 MHz

- Typical Doherty single-carrier W-CDMA performance:  $V_{DD} = 28$  Vdc,  $I_{DQA} = 400$  mA,  $V_{GSB} = 0.2$  Vdc,  $P_{out} = 28$  W Avg., input signal PAR = 9.9 dB @ 0.01% probability on CCDF.

Frequency	$G_{ps}$ (dB)	$\eta_D$ (%)	Output PAR (dB)	ACPR (dBc)
1880 MHz	16.8	45.8	8.3	–32.5
1960 MHz	17.0	47.7	8.2	–33.5
2025 MHz	16.5	47.9	8.0	–34.3

### Features

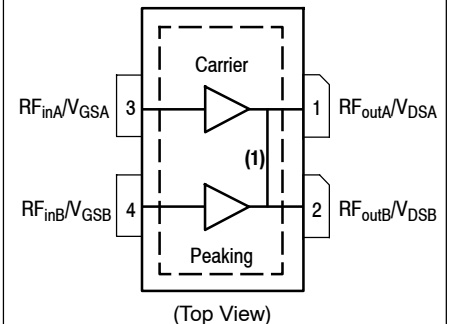
- Advanced high performance in-package Doherty
- Designed for wide instantaneous bandwidth applications
- Greater negative gate-source voltage range for improved Class C operation
- Able to withstand extremely high output VSWR and broadband operating conditions
- Designed for digital predistortion error correction systems

**A2T20H160W04NR3**

**1880–2025 MHz, 28 W AVG., 28 V  
AIRFAST RF POWER LDMOS  
TRANSISTOR**



**OM-780-4L  
PLASTIC**



Note: Exposed backside of the package is the source terminal for the transistor.

**Figure 1. Pin Connections**

- Pin connections 1 and 2 are DC coupled and RF independent.

**Table 1. Maximum Ratings**

Rating	Symbol	Value	Unit
Drain–Source Voltage	$V_{DS}$	–0.5, +65	Vdc
Gate–Source Voltage	$V_{GS}$	–6.0, +10	Vdc
Operating Voltage	$V_{DD}$	32, +0	Vdc
Storage Temperature Range	$T_{stg}$	–65 to +150	°C
Case Operating Temperature Range	$T_C$	–40 to +125	°C
Operating Junction Temperature Range (1,2)	$T_J$	–40 to +225	°C

**Table 2. Thermal Characteristics**

Characteristic	Symbol	Value (2,3)	Unit
Thermal Resistance, Junction to Case Case Temperature 75°C, 28 W Avg., W-CDMA, 28 Vdc, $I_{DQA} = 400$ mA, $V_{GSB} = 0.2$ Vdc, $f = 1960$ MHz	$R_{\theta JC}$	0.45	°C/W

**Table 3. ESD Protection Characteristics**

Test Methodology	Class
Human Body Model (per JESD22-A114)	2
Machine Model (per EIA/JESD22-A115)	B
Charge Device Model (per JESD22-C101)	IV

**Table 4. Moisture Sensitivity Level**

Test Methodology	Rating	Package Peak Temperature	Unit
Per JESD22-A113, IPC/JEDEC J-STD-020	3	260	°C

**Table 5. Electrical Characteristics** ( $T_A = 25^\circ\text{C}$  unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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**Off Characteristics (4)**

Zero Gate Voltage Drain Leakage Current ( $V_{DS} = 65$ Vdc, $V_{GS} = 0$ Vdc)	$I_{DSS}$	—	—	10	$\mu\text{Adc}$
Zero Gate Voltage Drain Leakage Current ( $V_{DS} = 32$ Vdc, $V_{GS} = 0$ Vdc)	$I_{DSS}$	—	—	5	$\mu\text{Adc}$
Gate–Source Leakage Current ( $V_{GS} = 5$ Vdc, $V_{DS} = 0$ Vdc)	$I_{GSS}$	—	—	1	$\mu\text{Adc}$

**On Characteristics - Side A, Carrier**

Gate Threshold Voltage ( $V_{DS} = 10$ Vdc, $I_D = 80$ $\mu\text{Adc}$ )	$V_{GS(th)}$	1.4	1.8	2.2	Vdc
Gate Quiescent Voltage ( $V_{DD} = 28$ Vdc, $I_{DA} = 400$ mAdc, Measured in Functional Test)	$V_{GSA(Q)}$	2.2	2.6	3.0	Vdc
Drain–Source On–Voltage ( $V_{GS} = 10$ Vdc, $I_D = 0.8$ Adc)	$V_{DS(on)}$	0.1	0.15	0.3	Vdc

**On Characteristics - Side B, Peaking**

Gate Threshold Voltage ( $V_{DS} = 10$ Vdc, $I_D = 110$ $\mu\text{Adc}$ )	$V_{GS(th)}$	0.8	1.2	1.6	Vdc
Drain–Source On–Voltage ( $V_{GS} = 10$ Vdc, $I_D = 1.1$ Adc)	$V_{DS(on)}$	0.1	0.15	0.3	Vdc

1. Continuous use at maximum temperature will affect MTTF.
2. MTTF calculator available at <http://www.nxp.com/RF/calculators>.
3. Refer to AN1955, *Thermal Measurement Methodology of RF Power Amplifiers*. Go to <http://www.nxp.com/RF> and search for AN1955.
4. Side A and Side B are tied together for these measurements.

(continued)

**Table 5. Electrical Characteristics** ( $T_A = 25^\circ\text{C}$  unless otherwise noted) (continued)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>Functional Tests</b> <sup>(1,2,3)</sup> (In NXP Doherty Test Fixture, 50 ohm system) $V_{DD} = 28\text{ Vdc}$ , $I_{DQA} = 400\text{ mA}$ , $V_{GSB} = 0.2\text{ Vdc}$ , $P_{out} = 28\text{ W Avg.}$ , $f = 1960\text{ MHz}$ , Single-Carrier W-CDMA, IQ Magnitude Clipping, Input Signal PAR = 9.9 dB @ 0.01% Probability on CCDF. ACPR measured in 3.84 MHz Channel Bandwidth @ $\pm 5\text{ MHz}$ Offset.					
Power Gain	$G_{ps}$	16.0	17.0	19.0	dB
Drain Efficiency	$\eta_D$	45.0	47.7	—	%
Output Peak-to-Average Ratio @ 0.01% Probability on CCDF	PAR	7.75	8.2	—	dB
Adjacent Channel Power Ratio	ACPR	—	-33.5	-28.0	dBc

**Load Mismatch** <sup>(3)</sup> (In NXP Doherty Test Fixture, 50 ohm system)  $I_{DQA} = 400\text{ mA}$ ,  $V_{GSB} = 0.2\text{ Vdc}$ ,  $f = 1960\text{ MHz}$

VSWR 10:1 at 32 Vdc, 158 W CW Output Power (3 dB Input Overdrive from 90 W CW Rated Power)	No Device Degradation
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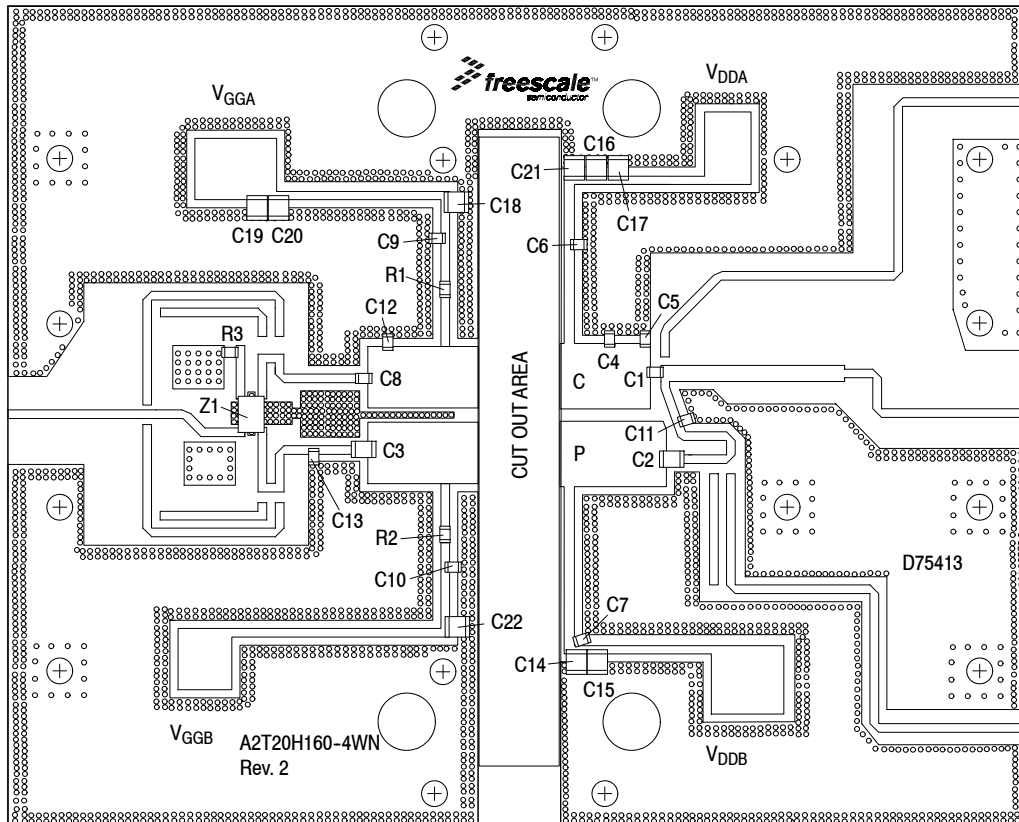
**Typical Performance** <sup>(3)</sup> (In NXP Doherty Test Fixture, 50 ohm system)  $V_{DD} = 28\text{ Vdc}$ ,  $I_{DQA} = 400\text{ mA}$ ,  $V_{GSB} = 0.2\text{ Vdc}$ , 1880–2025 MHz Bandwidth

$P_{out}$ @ 1 dB Compression Point, CW	P1dB	—	90	—	W
$P_{out}$ @ 3 dB Compression Point <sup>(4)</sup>	P3dB	—	200	—	W
AM/PM (Maximum value measured at the P3dB compression point across the 1880–2025 MHz bandwidth)	$\Phi$	—	-9.1	—	°
VBW Resonance Point (IMD Third Order Intermodulation Inflection Point)	$VBW_{res}$	—	140	—	MHz
Gain Flatness in 145 MHz Bandwidth @ $P_{out} = 28\text{ W Avg.}$	$G_F$	—	0.5	—	dB
Gain Variation over Temperature (-30°C to +85°C)	$\Delta G$	—	0.002	—	dB/°C
Output Power Variation over Temperature (-30°C to +85°C)	$\Delta P1dB$	—	0.003	—	dB/°C

**Table 6. Ordering Information**

Device	Tape and Reel Information	Package
A2T20H160W04NR3	R3 Suffix = 250 Units, 32 mm Tape Width, 13-inch Reel	OM-780-4L

1.  $V_{DDA}$  and  $V_{ddb}$  must be tied together and powered by a single DC power supply.
2. Part internally matched both on input and output.
3. Measurement made with device in an asymmetrical Doherty configuration.
4.  $P3dB = P_{avg} + 7.0\text{ dB}$  where  $P_{avg}$  is the average output power measured using an unclipped W-CDMA single-carrier input signal where output PAR is compressed to 7.0 dB @ 0.01% probability on CCDF.



\*C2 and C3 are mounted vertically.

Note:  $V_{DDA}$  and  $V_{DDB}$  must be tied together and powered by a single DC power supply.

**Figure 2. A2T20H160W04NR3 Test Circuit Component Layout**

**Table 7. A2T20H160W04NR3 Test Circuit Component Designations and Values**

Part	Description	Part Number	Manufacturer
C1	6.8 pF Chip Capacitor	ATC600F6R8BT250XT	ATC
C2, C3	12 pF Chip Capacitors	ATC100B120JT500XT	ATC
C4	1.2 pF Chip Capacitor	ATC600F1R2BT250XT	ATC
C5	0.6 pF Chip Capacitor	ATC600F0R6BT250XT	ATC
C6, C7, C8, C9, C10	12 pF Chip Capacitors	ATC600F120JT250XT	ATC
C11	0.4 pF Chip Capacitor	ATC600F0R4BT250XT	ATC
C12, C13	0.5 pF Chip Capacitors	ATC600F0R5BT250XT	ATC
C14, C15, C16, C17, C18, C19, C20, C21, C22	10 $\mu$ F Chip Capacitors	GRM32ER61H106KA12L	Murata
R1, R2	3.3 $\Omega$ , 1/2 W Chip Resistors	ERJ-14YJ3R3U	Panasonic
R3	50 $\Omega$ , 4 W Chip Resistor	CW12010T0050GBK	ATC
Z1	1800–2200 MHz Band, 90°, 2 dB Directional Coupler	X3C20F1-02S	Anaren
PCB	Rogers RO4350B, 0.020", $\epsilon_r = 3.66$	D75413	MTL

## TYPICAL CHARACTERISTICS — 1880–2025 MHz

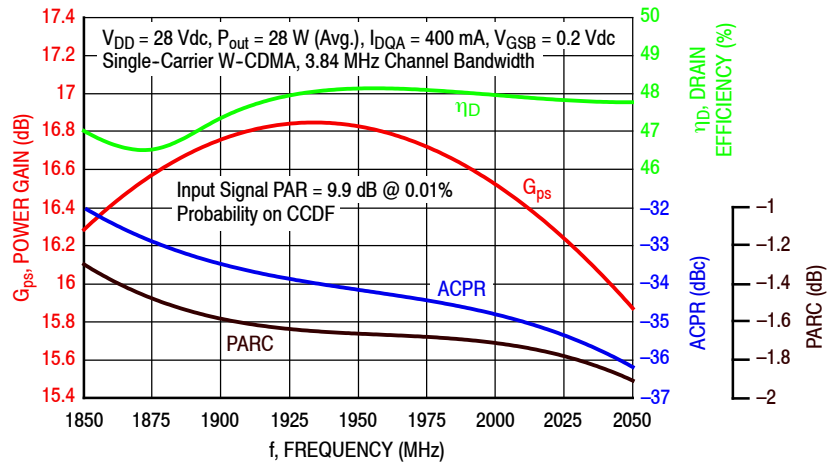


Figure 3. Single-Carrier Output Peak-to-Average Ratio Compression (PARC) Broadband Performance @  $P_{out} = 28$  Watts Avg.

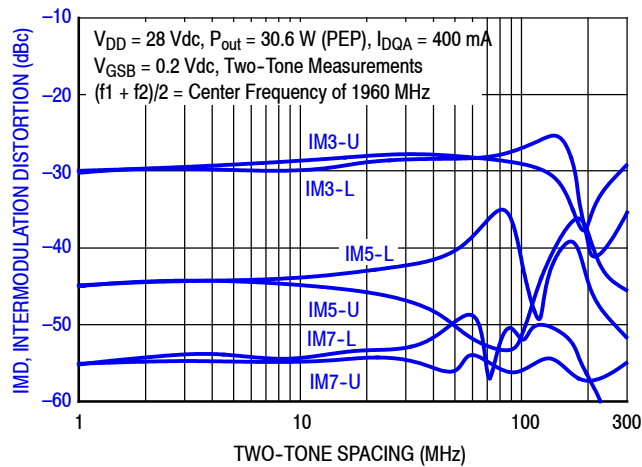


Figure 4. Intermodulation Distortion Products versus Two-Tone Spacing

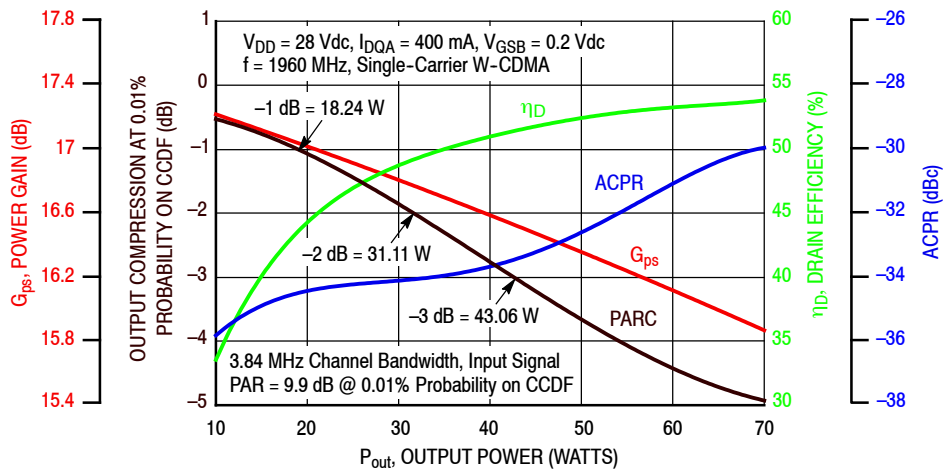
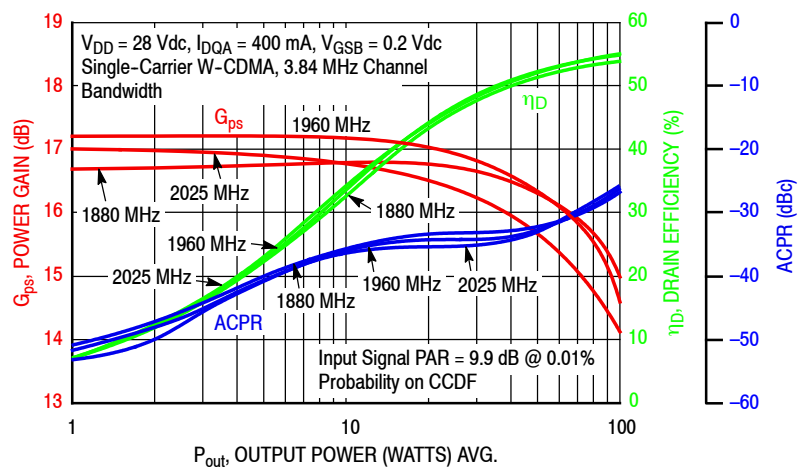
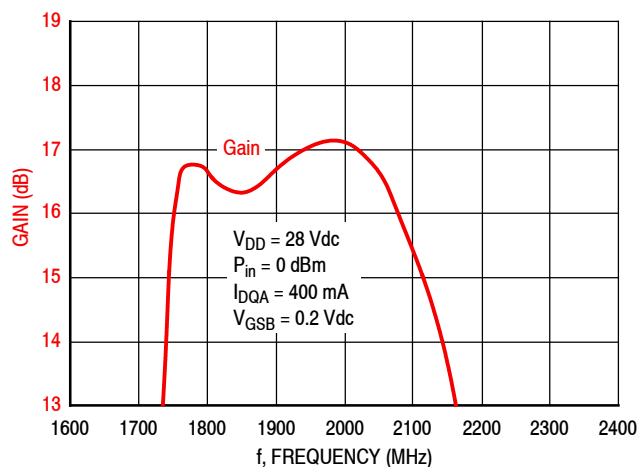


Figure 5. Output Peak-to-Average Ratio Compression (PARC) versus Output Power

## TYPICAL CHARACTERISTICS — 1880–2025 MHz

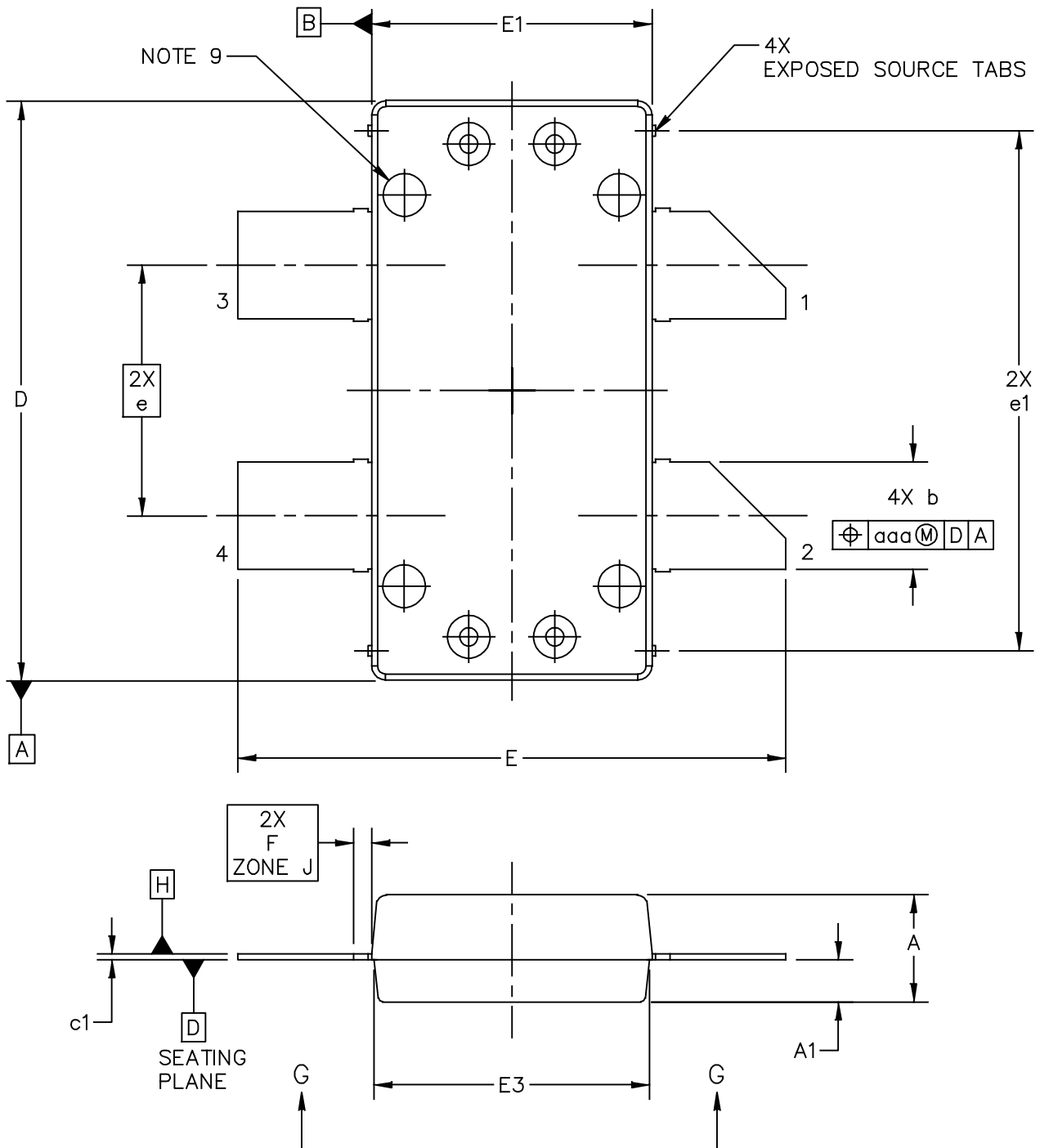


**Figure 6. Single-Carrier W-CDMA Power Gain, Drain Efficiency and ACPR versus Output Power**



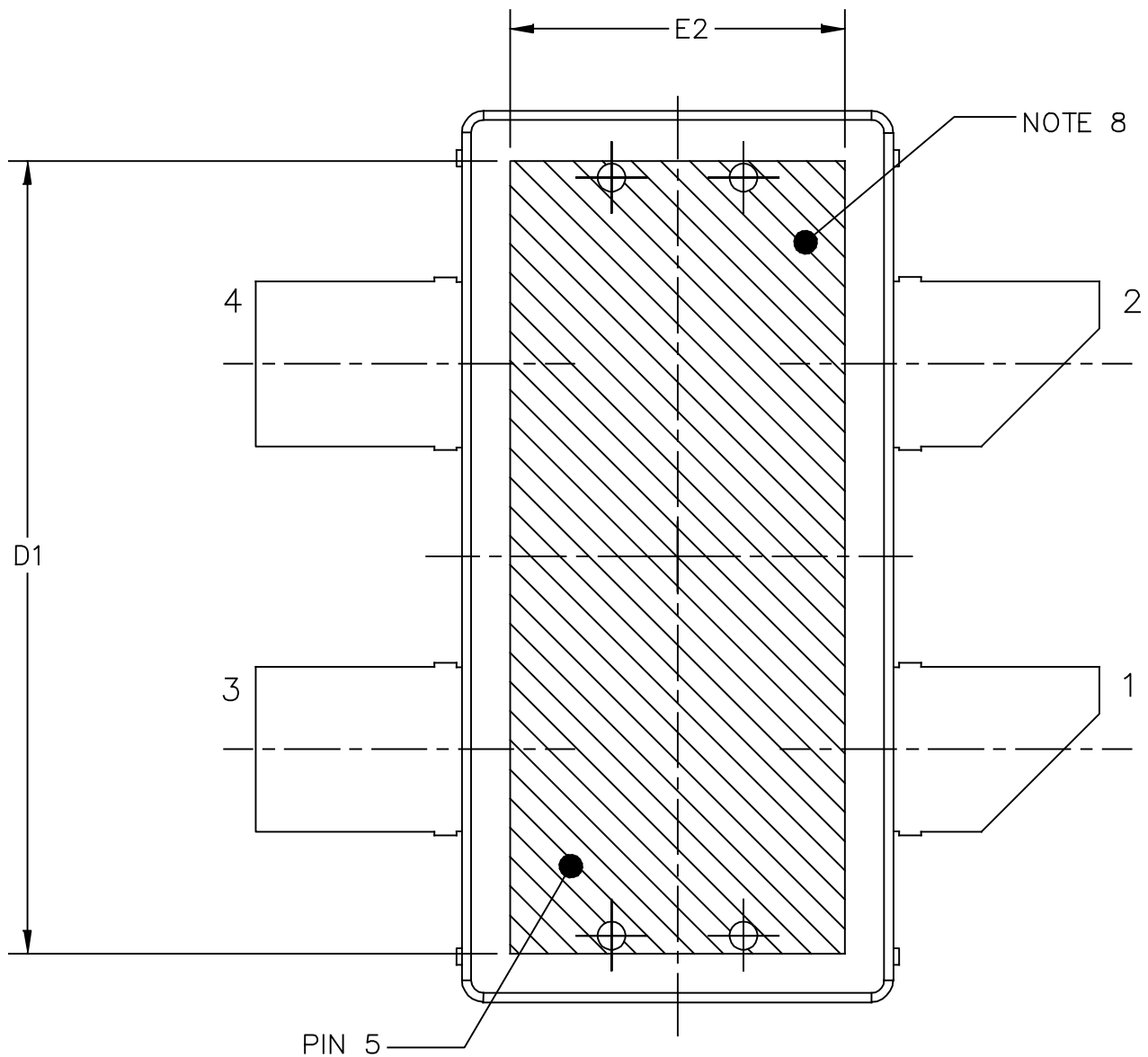
**Figure 7. Broadband Frequency Response**

# PACKAGE DIMENSIONS



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TITLE:  OM780-4 STRAIGHT LEAD	DOCUMENT NO: 98ASA10833D REV: B	
	STANDARD: NON-JEDEC	
	SOT1818-4	16 MAR 2016

A2T20H160W04NR3



BOTTOM VIEW  
VIEW G-G

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		SOT1818-4	16 MAR 2016



NOTES:

1. CONTROLLING DIMENSION: INCH
2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M-1994.
3. DATUM PLANE -H- IS LOCATED AT TOP OF LEAD AND IS COINCIDENT WITH THE LEAD WHERE THE LEAD EXITS THE PLASTIC BODY AT THE TOP OF THE PARTING LINE.
4. DIMENSIONS "D" AND "E1" DO NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS .006 PER SIDE. DIMENSIONS "D AND "E1" DO INCLUDE MOLD MISMATCH AND ARE DETERMINED AT DATUM PLANE -H-.
5. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE .005 TOTAL IN EXCESS OF THE b DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. DATUMS -A- AND -B- TO BE DETERMINED AT DATUM PLANE -H-.
7. DIMENSION A1 APPLIES WITHIN ZONE "J" ONLY.
8. HATCHING REPRESENTS THE EXPOSED AREA OF THE HEAT SLUG. THE DIMENSIONS D1 AND E2 REPRESENT THE VALUES BETWEEN THE TWO OPPOSITE POINTS ALONG THE EDGES OF EXPOSED AREA OF HEAT SLUG.
9. DIMPLED HOLE REPRESENTS INPUT SIDE.

INCH			MILLIMETER		INCH			MILLIMETER	
DIM	MIN	MAX	MIN	MAX	DIM	MIN	MAX	MIN	MAX
A	0.148	.152	3.76	3.86	b	.147	.153	3.73	3.89
A1	.059	.065	1.50	1.65	c1	.007	.011	0.18	0.28
D	.808	.812	20.52	20.62	e	.350 BSC		8.89 BSC	
D1	.720	----	18.29	----	e1	.721	.729	18.31	18.52
E	.762	.770	19.36	19.56	aaa	.004	0.10		
E1	.390	.394	9.91	10.01					
E2	.306	----	7.77	----					
E3	.383	.387	9.72	9.83					
F	.025 BSC		0.635 BSC						
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					STANDARD: NON—JEDEC				
					SOT1818—4    16 MAR 2016				

## PRODUCT DOCUMENTATION, SOFTWARE AND TOOLS

Refer to the following resources to aid your design process.

### Application Notes

- AN1907: Solder Reflow Attach Method for High Power RF Devices in Over-Molded Plastic Packages
- AN1955: Thermal Measurement Methodology of RF Power Amplifiers

### Engineering Bulletins

- EB212: Using Data Sheet Impedances for RF LDMOS Devices

### Software

- Electromigration MTTF Calculator
- .s2p File

### Development Tools

- Printed Circuit Boards

### To Download Resources Specific to a Given Part Number:

1. Go to <http://www.nxp.com/RF>
2. Search by part number
3. Click part number link
4. Choose the desired resource from the drop down menu

## REVISION HISTORY

The following table summarizes revisions to this document.

Revision	Date	Description
0	Aug. 2016	<ul style="list-style-type: none"><li>• Initial release of data sheet</li></ul>

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